

### CTH214 Series

# AC Input 4-Pin Half Pitch Mini-Flat DMC-Isolator® Phototransistor Optocoupler

#### **Features**

- High isolation 3750 VRMS
- Patented coplanar structure DMC-Isolator®
- Various CTR selection available
- AC input with transistor output
- Operating Temperature range 55 °C to 110 °C
- External Creepage ≥ 5.0mm
- Distance Through Isolation ≥ 0.4mm
- Clearance Distance ≥ 5.0mm
- RoHS and REACH compliance
- Halogen Free compliance
- MSL class 1
- Regulatory Approvals
  - ✓ UL UL1577 (E364000)
  - ✓ VDE EN60747-5-5 (VDE0884-5)
  - ✓ CQC GB4943.1, GB8898 (15001123951)

✓ IEC62368 (FI/41119)

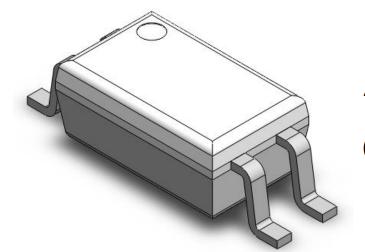
#### **Description**

The CTH214 series consists of a phototransistor optically coupled to two Infrared-emitting diodes, connected in inverse parallel in a 4-lead half pitch Mini-Flat DMC-Isolator® package.

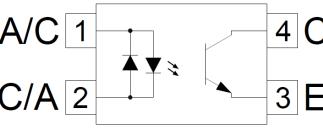
### **Applications**

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

# **Package Outline**



### **Schematic**





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# Absolute Maximum Ratings $T_A = 25$ °C, unless otherwise specified

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage (AC, 1 minute, 40 ~ 60% R.H.)	3750	V <sub>RMS</sub>	
Ртот	Total power dissipation	200	mW	
Topr	Operating temperature	-55 ~ +110	°C	
Tstg	Storage temperature	-55 ~ +150	°C	
TsoL	Soldering temperature (For 10 seconds)	260	°C	
Emitter			·	
l <sub>F</sub>	Forward current	±50	mA	
I <sub>F(TRANS)</sub>	Peak transient current (≤1µs P.W,300pps)	1	А	
P <sub>D</sub>	Emitter power dissipation	70	mW	
Detector		•		
PD	Detector power dissipation	150	mW	
B <sub>VCEO</sub>	Collector-Emitter Breakdown Voltage	80	V	
Bveco	Emitter-Collector Breakdown Voltage	7	V	
Ic	Collector Current	50	mA	





# **Electrical Characteristics** $T_A = 25^{\circ}\text{C}$ , unless otherwise specified

#### **Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I <sub>F</sub> =±10mA		1.24	1.4	V	
Cin	Input Capacitance	f= 1MHz	-	30	-	pF	

#### **Detector Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
B <sub>VCEO</sub>	Collector-Emitter Breakdown	Ic= 100μA	80	-	-	V	
B <sub>VECO</sub>	Emitter-Collector Breakdown	I <sub>E</sub> = 100μA	7	-	-	V	
ICEO	Collector-Emitter Dark Current	V <sub>CE</sub> = 20V, I <sub>F</sub> =0mA	-	-	100	nA	

#### **Transfer Characteristics**

Symbol	Parameters		Test Conditions	Min	Тур	Max	Units	Notes
	Current Transfer	CTH214		20	-	300		
CTR	Current Transfer Ratio	CTH214A	I <sub>F</sub> = ±1mA, V <sub>CE</sub> = 5V	50	-	150	%	
	Ratio	CTH214B		100		300		
CTD	Current Transfer	CTH214	l- , ε ω Λ . \ / Ε \ /	30	-	600	- %	
CTR	Ratio	CTH214A	I <sub>F</sub> = ±5mA, V <sub>CE</sub> = 5V	80	-	300		
	CTR Symmetry		I <sub>F</sub> = ±1mA, V <sub>CE</sub> = 5V	0.7	-	1.3		
V	Collector-Emitter Satur	ation	I <sub>F</sub> = +20mA, I <sub>C</sub> = 1mA		0.04	0.2	V	
V <sub>CE</sub> (SAT)	Voltage		F= ±20MA, IC= MIA	-	0.04	0.2	V	
R <sub>IO</sub>	Isolation Resistance		V <sub>IO</sub> = 500V <sub>DC</sub> , 40 ~ 60% R.H.	5x10 <sup>10</sup>	-	-	Ω	
Cıo	Isolation Capacitance		f= 1MHz	-	0.5	1	pF	

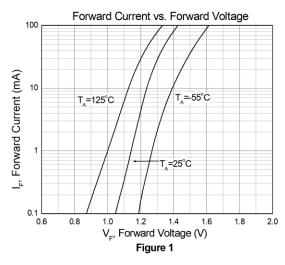
### **Switching Characteristics**

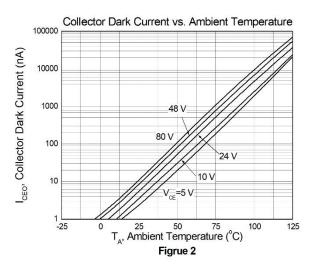
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
tr	Rise Time	L 2m/ V 2V/ B: - 1000		6	18	0	
t <sub>f</sub>	Fall Time	$I_C$ = 2mA, $V_{CE}$ = 2V, $R_L$ = 100 $\Omega$	-	8	18	μS	

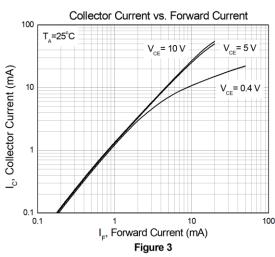


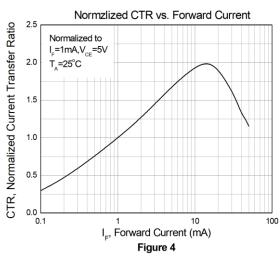


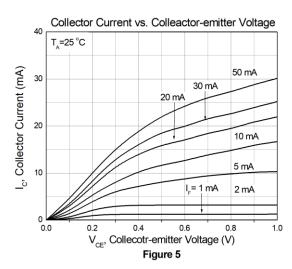
#### Typical Characteristic Curves $T_A = 25^{\circ}C$ , unless otherwise specified

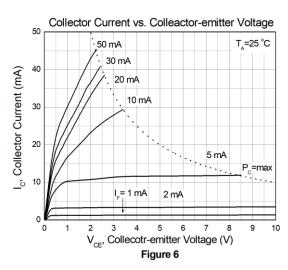








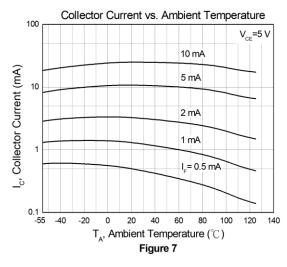


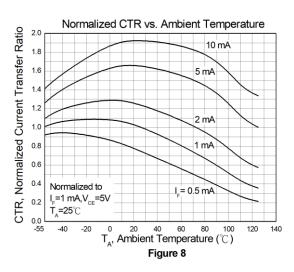


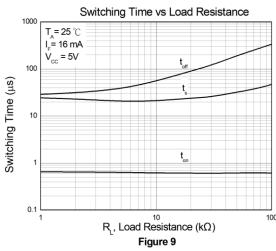


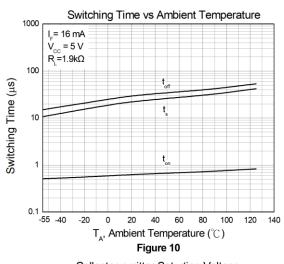


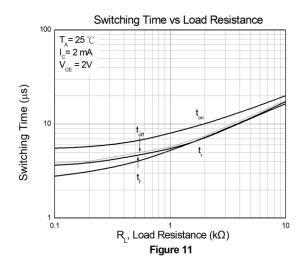
# Typical Characteristic Curves $\tau_A = 25$ °C, unless otherwise specified (Continued)

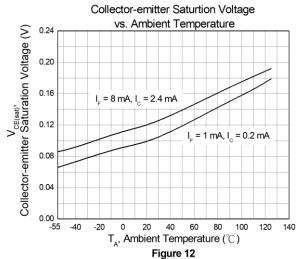








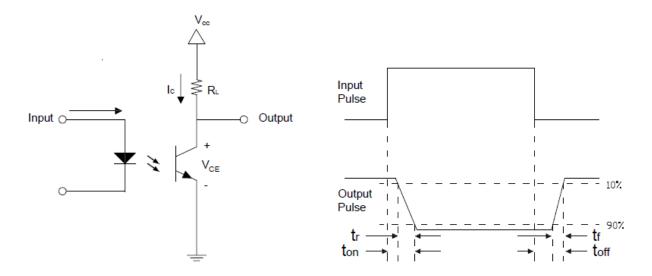








### **Test Circuit**

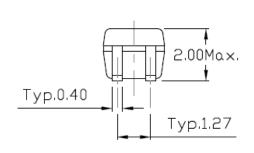


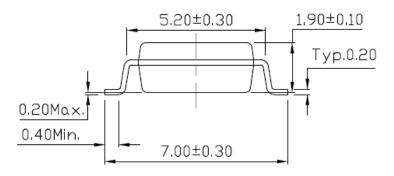
**Figure 13: Switching Time Test Circuits** 

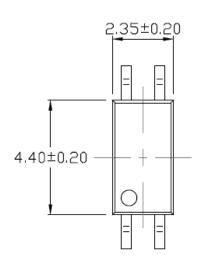


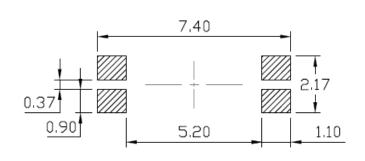


### Package Dimension Dimensions in mm unless otherwise stated









# **Marking Information**



#### Note:

CT : Denotes "CT Micro"

214 : Part Number

X : CTR Rank Option (Blank, A or B)V : VDE Safety Mark Option(Blank or V)

Y : One Digit Year CodeWW : Two Digit Work WeekK : Manufacturing Code





# **Ordering Information**

# CTH214X(V)(Z)

CT = Denotes "CT Micro"

H214 = Part Number

X = CTR Rank Option (Blank, A or B)

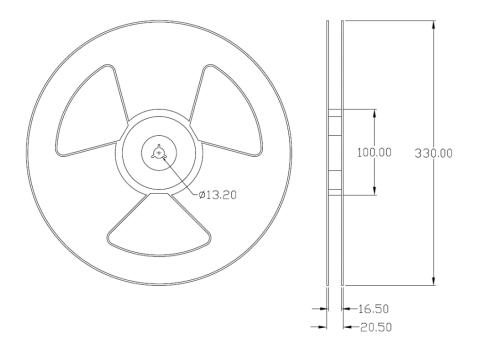
V = VDE Safety Mark Option (Blank or V)

Z = Tape and Reel Option (Blank, T1 or T2)

Option Description		Quantity
T1	Surface Mount Lead Forming – With Option 1 Taping	5000 Units/Reel
T2	Surface Mount Lead Forming – With Option 2 Taping	5000 Units/Reel

# Reel Dimension All dimensions are in mm, unless otherwise stated

### Option T1/T2



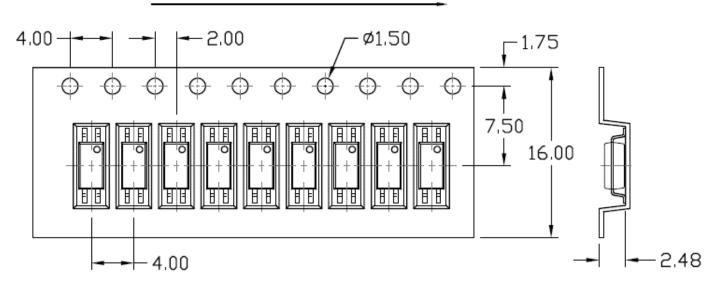




### Carrier Tape Specifications Dimensions in mm unless otherwise stated

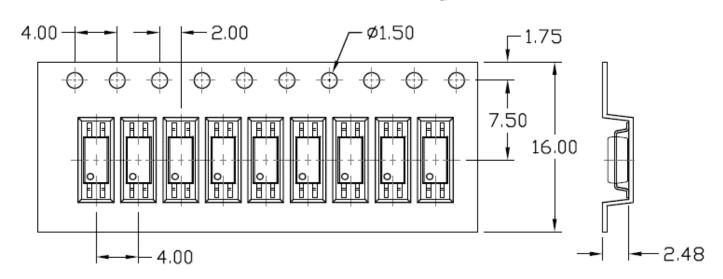
# Option (T1)

# Input Direction



### Option (T2)

# Input Direction





### Solderability spec (Follow the JEDEC standard JESD22-B102)

Reflow Soldering: Immersed surface, other than the end of pin as cut-surface, must be covered by solder.

Solder-Bath: More than 95% of the electrode must be covered with solder.

### **Wave soldering (Follow the JEDEC standard JESD22-A111)**

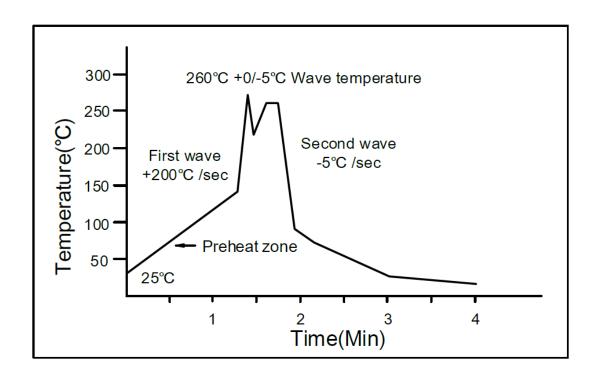
One time soldering is recommended within the condition of temperature.

Temperature: 260+0/-5°C.

Time: 10 sec.

Preheat temperature: 25 to 140°C.

Preheat time: 30 to 80 sec.



# Iron soldering (Follow the standard MIL-STD 202G, Method 210F)

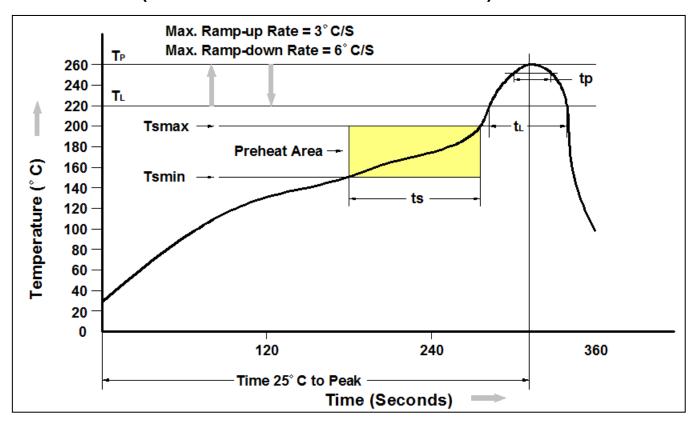
Allow single lead soldering in every single process.

One time soldering is recommended. Temperature: 350±10°C

Time: 5 sec max.



# Reflow Profile (Follow the JEDEC standard J-STD-020)



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t₂)	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.